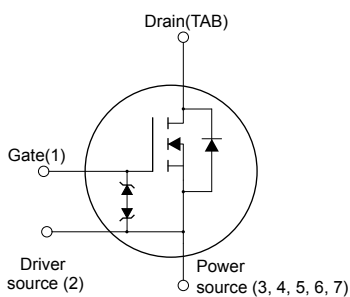
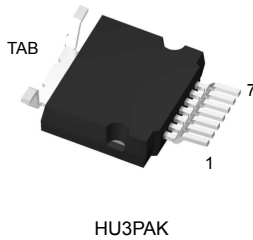


Automotive-grade N-channel 600 V, 84 mΩ typ., 29 A MDmesh DM6 Power MOSFET in an HU3PAK package




N-chG1DS2PS34567DTABZ



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STHU36N60DM6AG	600 V	99 mΩ	29 A

- AEC-Q101 qualified 
- Fast-recovery body diode
- Lower R_{DS(on)} per area vs previous generation
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected
- Excellent switching performance thanks to the extra driving source pin

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM6 fast-recovery diode series. Compared with the previous MDmesh fast generation, DM6 combines very low recovery charge (Q_{rr}), recovery time (t_{rr}) and excellent improvement in R_{DS(on)} per area with one of the most effective switching behaviors available in the market for the most demanding high-efficiency bridge topologies and ZVS phase-shift converters.

Product status link

[STHU36N60DM6AG](#)

Product summary

Order code	STHU36N60DM6AG
Marking	36N60DM6
Package	HU3PAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	29	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	18	
$I_D^{(1)}$	Drain current (pulsed)	103	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	210	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	100	V/ns
$di/dt^{(3)}$	Peak diode recovery current slope	1000	A/ μs
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	100	V/ns
T_J	Operating junction temperature range	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature range		$^\circ\text{C}$

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 29\text{ A}$, $V_{DS(peak)} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$
3. $V_{DS} \leq 480\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.6	$^\circ\text{C/W}$
$R_{thJB}^{(1)}$	Thermal resistance, junction-to-board	30	

1. When mounted on 1 inch² FR-4, 2 Oz copper board.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	6	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 100\text{ V}$)	630	mJ

2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified

Table 4. On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 600\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 600\text{ V}$, $T_C = 125\text{ }^\circ\text{C}^{(1)}$			200	
I_{GSS}	Gate body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 5	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3.25	4.00	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 14.5\text{ A}$		84	99	m Ω

1. Specified By Design – Not tested in production.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	1960	-	pF
C_{oss}	Output capacitance		-	140	-	pF
C_{rSS}	Reverse transfer capacitance		-	2	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}$, $V_{GS} = 0\text{ V}$	-	335	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.5	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}$, $I_D = 29\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 15. Test circuit for gate charge behavior)	-	46	-	nC
Q_{gs}	Gate-source charge		-	13	-	nC
Q_{gd}	Gate-drain charge		-	22	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 14.5\text{ A}$, $R_G = 4.7\text{ }\Omega$,	-	16	-	ns
t_r	Rise time	$V_{GS} = 10\text{ V}$	-	5.3	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 14. Switching times test circuit for resistive load and Figure 19. Switching time waveform)	-	50	-	ns
t_f	Fall time		-	7	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		29	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		103	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 29\text{ A}, V_{GS} = 0\text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 29\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_{DD} = 60\text{ V}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	110		ns
Q_{rr}	Reverse recovery charge		-	0.5		μC
I_{RRM}	Reverse recovery current		-	9		A
t_{rr}	Reverse recovery time	$I_{SD} = 29\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_{DD} = 60\text{ V},$ $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16. Test circuit for inductive load switching and diode recovery times)	-	215		ns
Q_{rr}	Reverse recovery charge		-	2		μC
I_{RRM}	Reverse recovery current		-	17		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

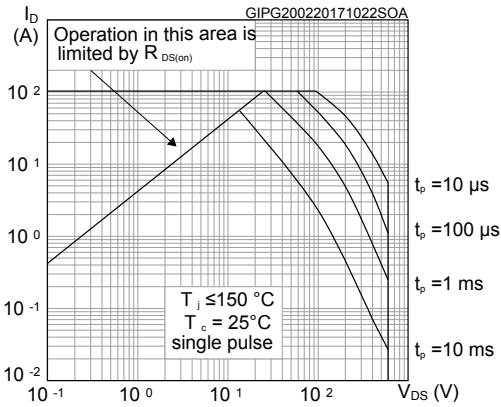


Figure 2. Thermal impedance

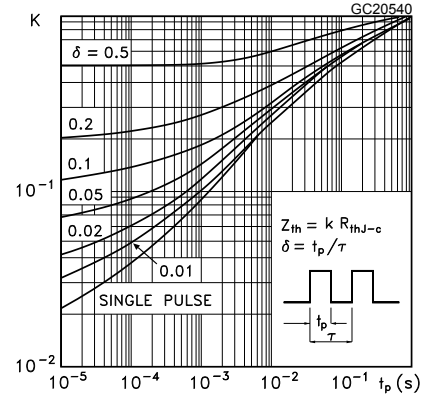


Figure 3. Output characteristics

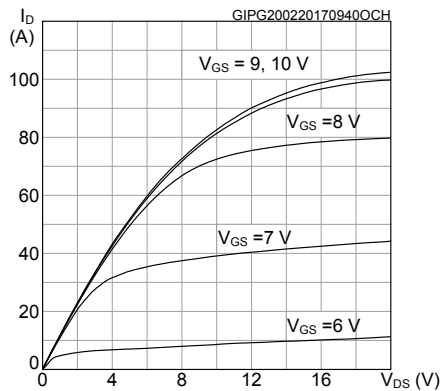


Figure 4. Transfer characteristics

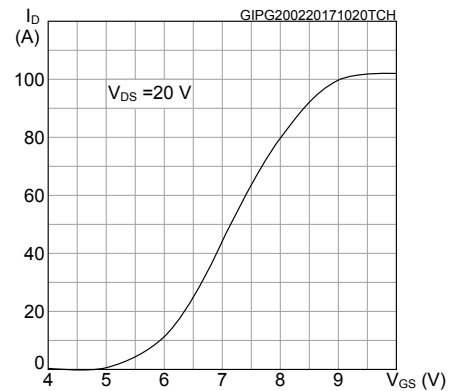


Figure 5. Gate charge vs gate-source voltage

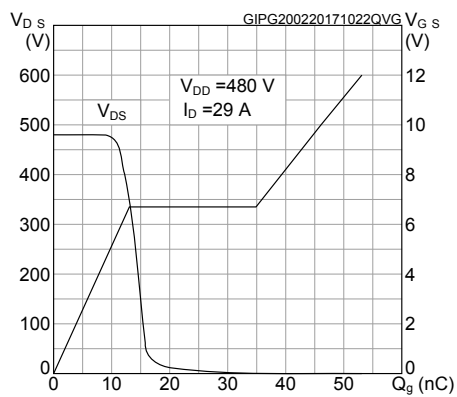


Figure 6. Static drain-source on-resistance

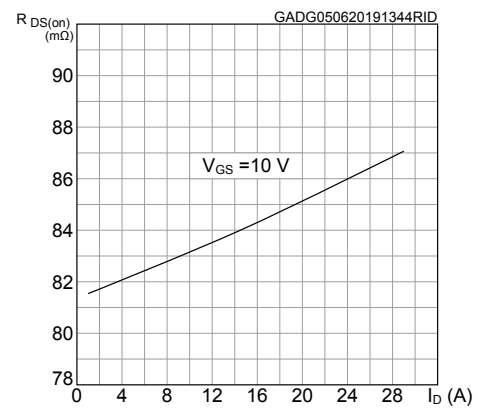


Figure 7. Capacitance variations

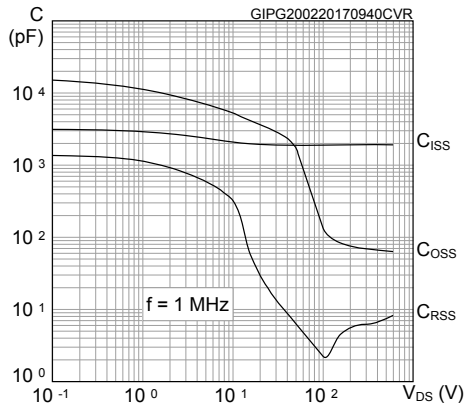


Figure 8. Normalized gate threshold voltage vs temperature

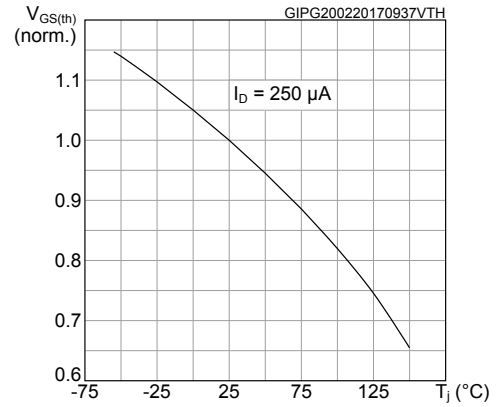


Figure 9. Normalized on-resistance vs temperature

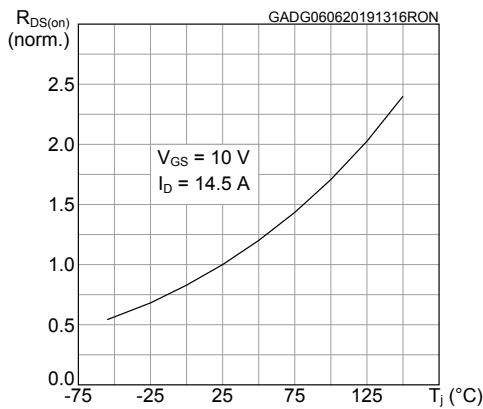


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

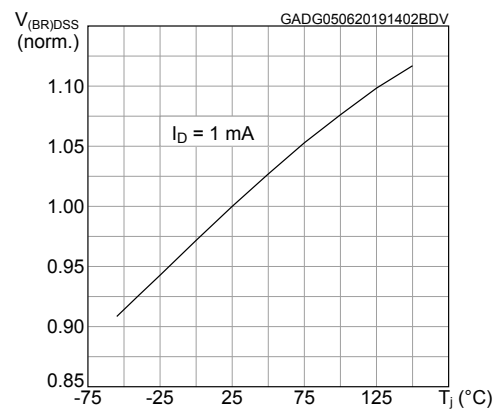


Figure 11. Source-drain diode forward characteristics

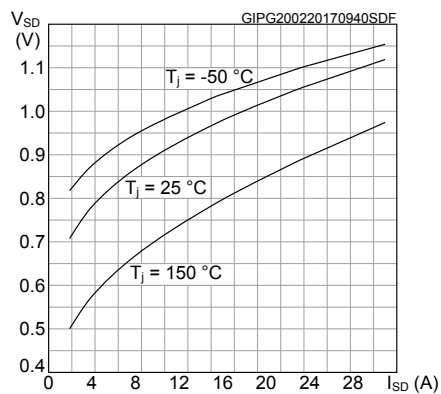
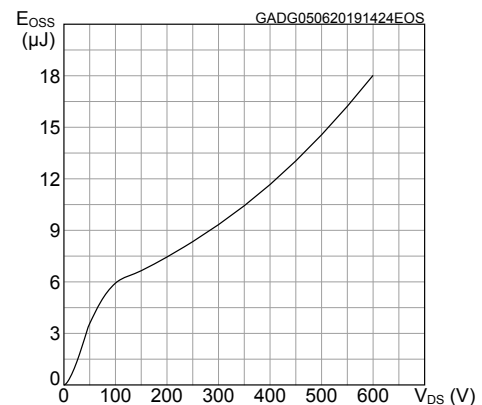
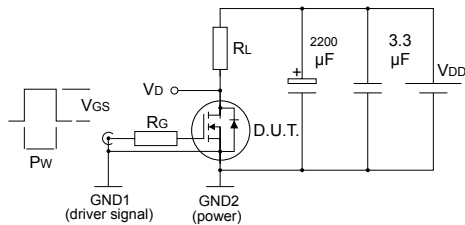


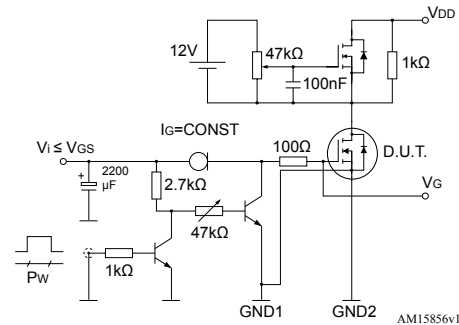
Figure 12. Output capacitance stored energy



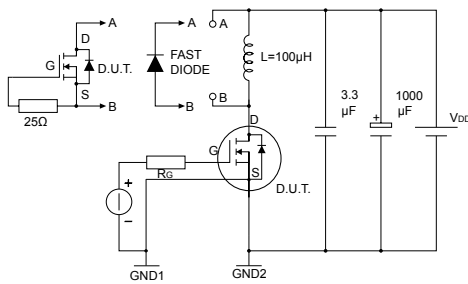
3 Test circuits

Figure 13. Switching times test circuit for resistive load


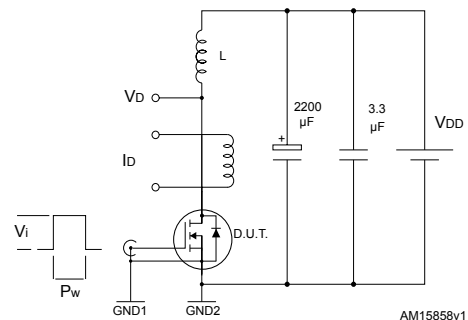
AM15855v1

Figure 14. Test circuit for gate charge behavior


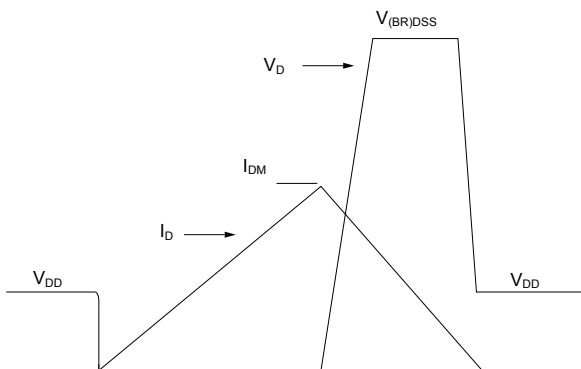
AM15856v1

Figure 15. Test circuit for inductive load switching and diode recovery times


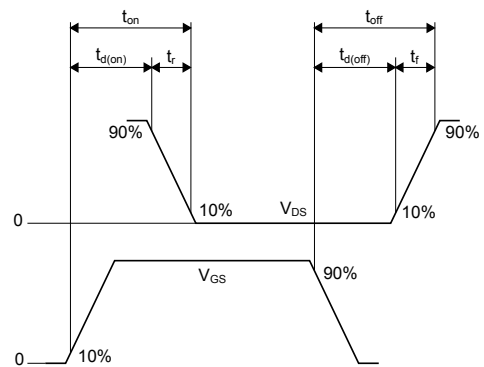
AM15857v1

Figure 16. Unclamped inductive load test circuit


AM15858v1

Figure 17. Unclamped inductive waveform


AM01472v1

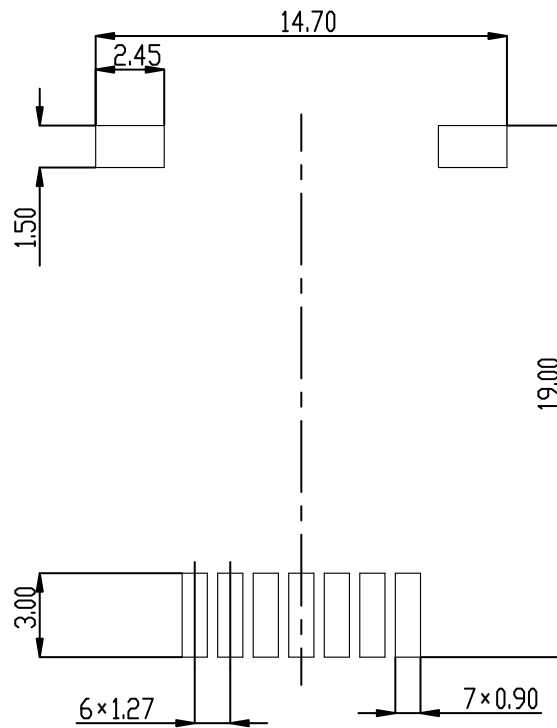
Figure 18. Switching time waveform


AM01473v1

Table 8. HU3PAK package mechanical data

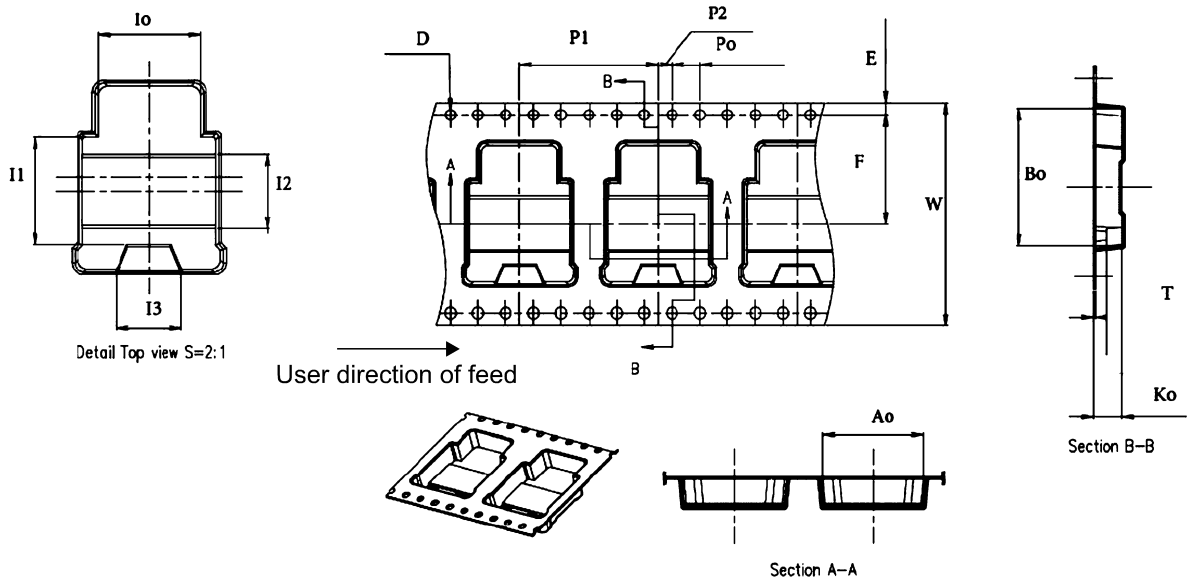
Ref.	Dimensions		
	mm		
	Min.	Typ.	Max.
A	3.40	3.50	3.60
A1		0.05	
b	0.50	0.60	0.70
b2	0.50	0.70	1.00
b3	0.80	0.90	1.00
c	0.40	0.50	0.60
c2	0.40	0.50	0.60
D	11.70	11.80	11.90
D1	8.80	8.955	9.10
E	13.90	14.00	14.10
E1	12.30	12.40	12.50
E2	7.75	7.80	7.85
e		1.27	
H	18.00	18.58	19.00
aaa		0.10	
L	2.40	2.52	2.60
L1		3.05	
L2	0.90	1.00	1.10
L3		0.26	
L4	0.075	0.125	0.175
L5	1.83	1.93	2.03
L6	2.14	2.24	2.34
L7	4.44	4.54	4.64
F1	2.90	3.00	3.10
F2	2.40	2.50	2.60
F3	0.25	0.35	0.45
N1	3.80	3.90	4.00
N2	0.25	0.30	0.45
N3	0.80	0.90	1.00
T	0.50	0.67	0.70
T2	9.18	9.38	9.43
V1		0°	8°
V2		0°	8°

Figure 20. HU3PAK recommended footprint (dimensions in mm)



4.2 HU3PAK packing information

Figure 21. HU3PAK carrier tape outline



DM00345054_3

Table 9. HU3PAK tape mechanical data

Dimension	Value
	mm
A0	14.40 ±0.10
B0	19.70
D	1.50 ±0.10
E	1.75 ±0.10
F	15.65 ±0.10
I0	11.00
I1	11.60 ±0.10
I2	8.00
I3	7.00
K0	4.20
P0	4.00 ±0.10
P1	20.00 ±0.10
P2	2.00 ±0.10
T	0.40 ±0.50
W	32.00 ±0.30

Figure 22. HU3PAK reel outline

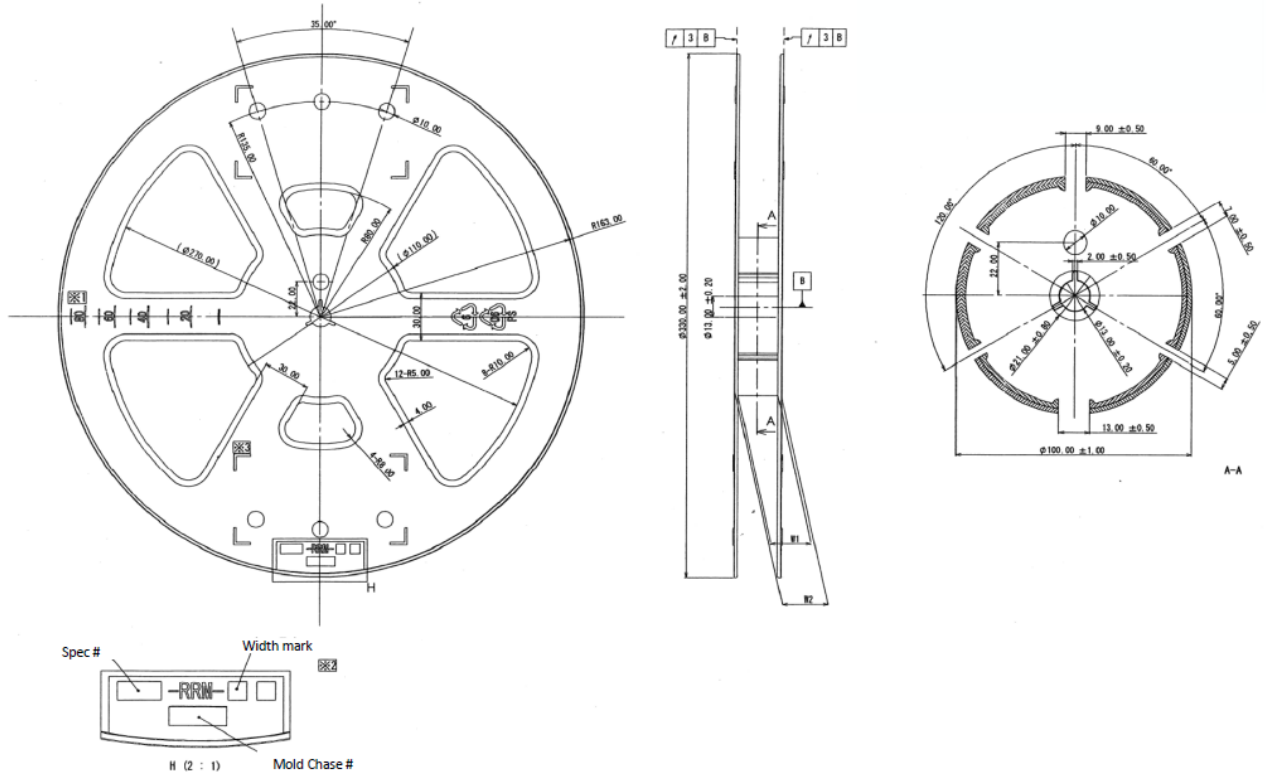


Table 10. HU3PAK reel mechanical data

Dimension	Value
	mm
Reel width	32.0
Reel inner width	33.4 ± 1.0
Reel outer width	37.4 ± 1.0

Revision history

Table 11. Document revision history

Date	Revision	Changes
05-Jun-2019	1	Initial release.
06-Oct-2021	2	Modified <i>Features</i> on cover page. Modified <i>Table 1. Absolute maximum ratings</i> and <i>Table 4. On/off-state</i> . Modified <i>Section 4 Package information</i> . Minor text changes.
11-Nov-2021	3	Modified <i>Table 1. Absolute maximum ratings</i> . Modified <i>Table 8. HU3PAK package mechanical data</i> . Minor text changes.

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